

What is Claimed is:

1. A semiconductor chip, comprising:
a surface protective film for covering internal
wiring;
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5 an external connection pad which is formed by
partially exposing said internal wiring from the
surface protective film; and

a wire connecting portion which is formed using
a metal material having oxidation resistance on the
10 external connection pad and to which a wire for
electrical connection to an external terminal is
connected.

Sub B 2. The semiconductor chip according to claim 1,
B wherein

15 said semiconductor chip is overlapped with and
joined to a surface of another solid device in a state
where said surface protective film is opposed to a
surface of the solid device.

JMB 3. The semiconductor chip according to claim 2,
20 further comprising

an internal connection pad which is formed by
partially exposing said internal wiring from said
surface protective film in a portion different from
said external connection pad, and

25 a bump formed in a raised state on the internal

connection pad using a metal material having oxidation resistance in order to make electrical connection to said solid device.

4. The semiconductor chip according to claim 2,
5 wherein

said solid device includes another semiconductor chip.

5. The semiconductor chip according to claim 1,
wherein

10 said wire connecting portion is composed of the same material as that for said bump.

6. A semiconductor device having a chip-on-chip structure in which a secondary chip is overlapped with and joined to a surface of a primary chip, wherein

15 said primary chip comprises

a surface protective film for covering internal wiring,

an external connection pad formed by partially exposing the internal wiring from the surface

20 protective film,

a wire connecting portion which is formed using a metal material having oxidation resistance on the external connection pad and to which a wire for electrical connection to an external terminal is connected,

an internal connection pad which is formed by partially exposing said internal wiring from said surface protective film in a portion different from said external connection pad, and

5 a bump which is formed in a raised state on the internal connection pad using a metal material having oxidation resistance for electrically connecting the primary chip and the secondary chip.

7. The semiconductor device according to claim
10 6, wherein

said wire connecting portion is composed of the same material as that for said bump.

8. A method of producing a semiconductor chip which is to be overlapped with and joined to a surface
15 of another solid device, comprising the steps of:

stacking a surface protective film on internal wiring;

forming an opening on the surface protective film to partially expose said internal wiring, to form an
20 external connection pad and an internal connection pad; and

selectively plating said external connection pad and the internal connection pad, to respectively form a wire connecting portion to which a wire for
25 electrical connection to an external terminal is

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connected and a bump for electrical connection to the other solid device.

9. A method of producing a semiconductor device having a chip-on-chip structure in which a secondary 5 chip is overlapped with and joined to a surface of a primary chip, comprising the steps of:

stacking a surface protective film on internal wiring in the primary chip;

10 forming an opening on said surface protective film to partially expose said internal wiring, to form an external connection and an internal connection;

and *B*

selectively plating said external connection pad and the internal connection pad, to respectively form 15 a wire connecting portion to which a wire for electrical connection to an external terminal is connected and a bump for electrical connection to said secondary chip; and

joining the primary chip and the secondary chip 20 to each other through said bump.

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